

FIG. 1 A

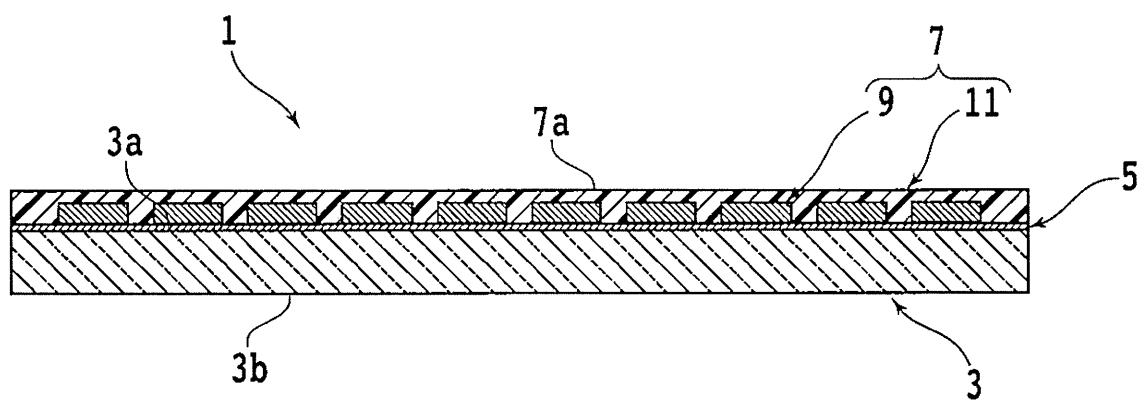


FIG. 1 B

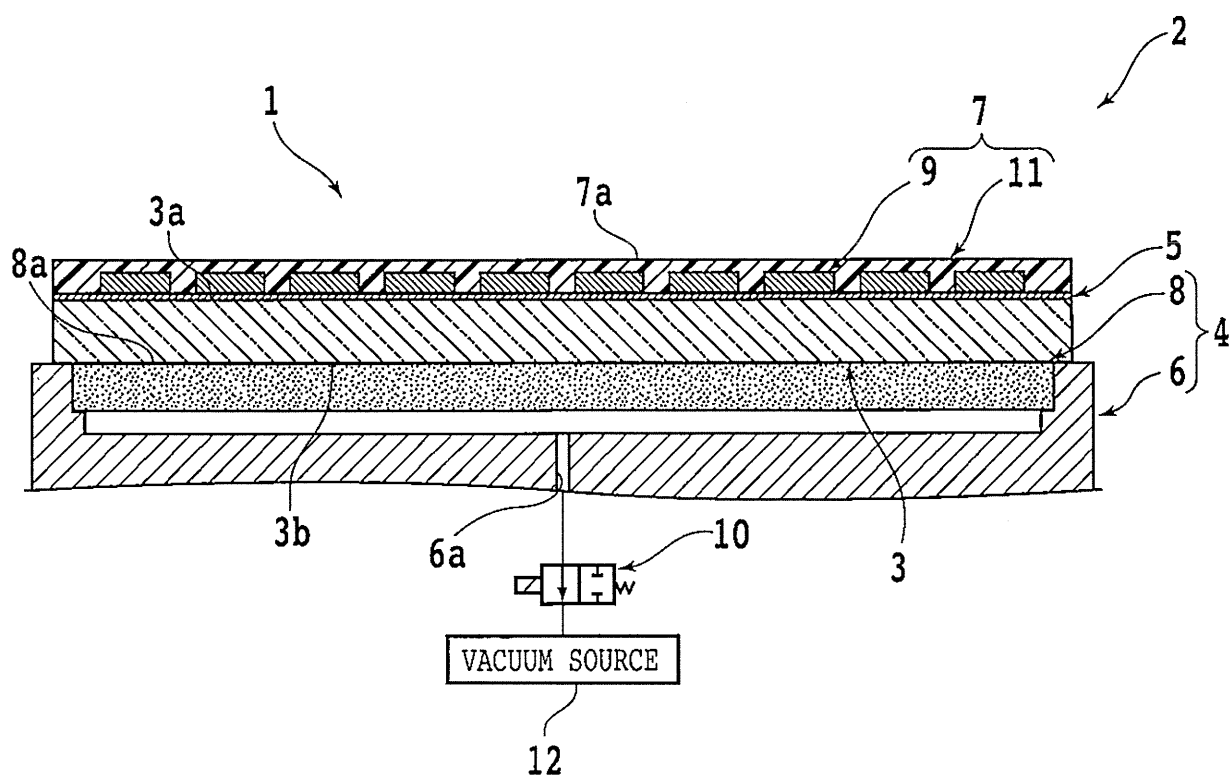


FIG.2A

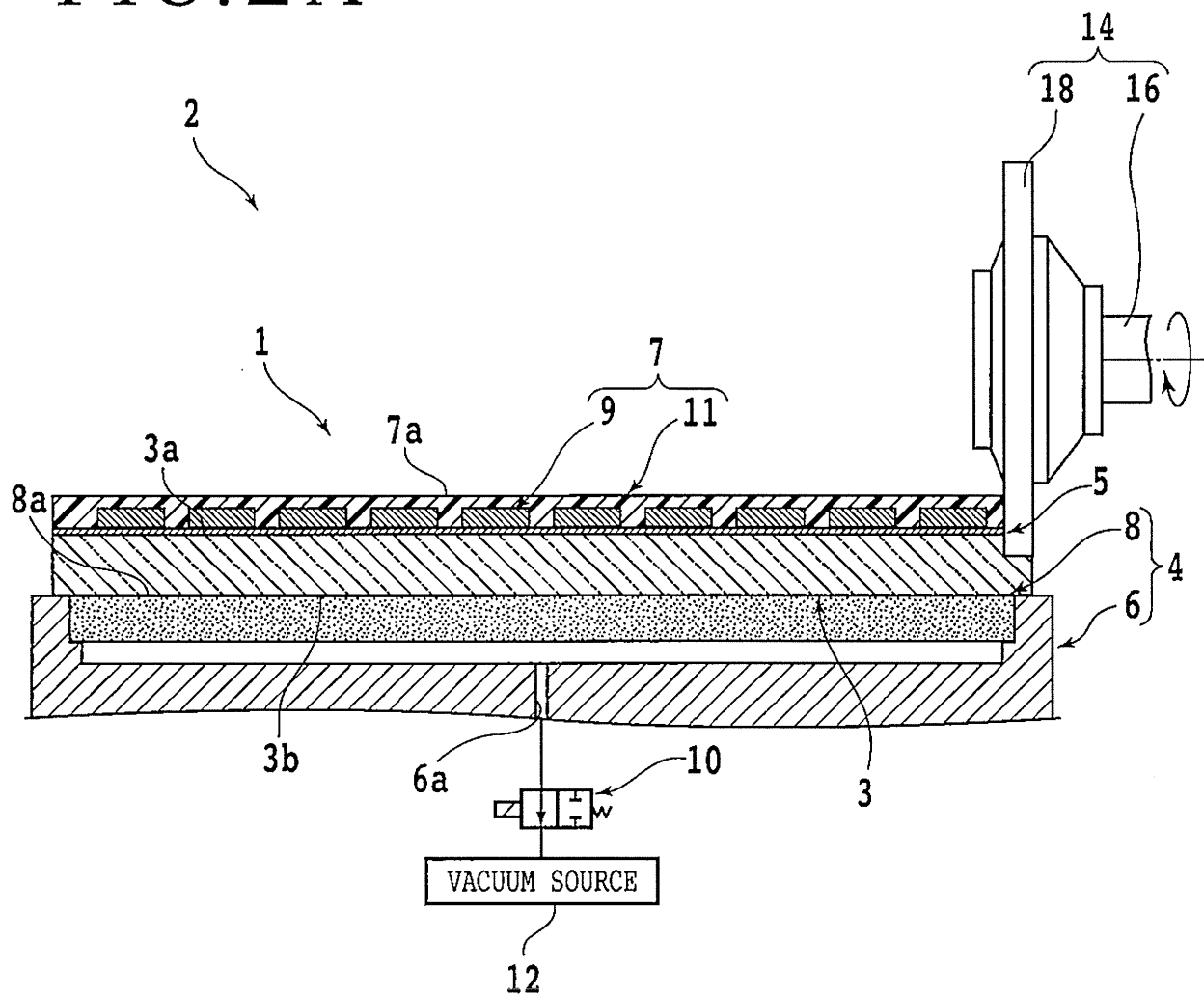
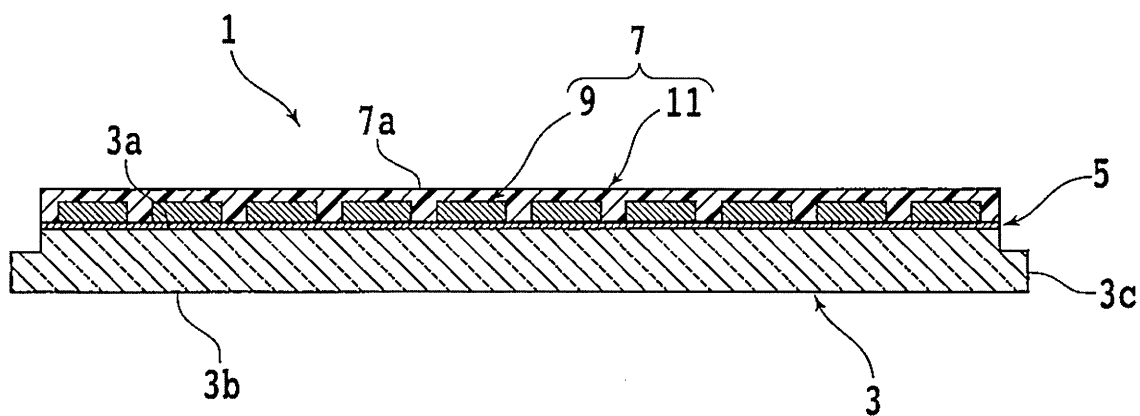


FIG.2B



A cross-sectional view of a semiconductor device 1. The device consists of a substrate 3 with a top surface 3a and a bottom surface 3b. A layer 24 is formed on the top surface 3a. A series of rectangular blocks 7 are formed on the layer 24. A layer 5 is formed on the top surface 3a, and a layer 9 is formed on the top surface 3a. A layer 11 is formed on the top surface 3a. A layer 22 is formed on the top surface 3a. A layer 24a is formed on the top surface 3a. A layer 3c is formed on the bottom surface 3b. A layer 3 is formed on the bottom surface 3b. A layer 24 is formed on the top surface 3a. A layer 7a is formed on the top surface 3a. A layer 7 is formed on the top surface 3a. A layer 11 is formed on the top surface 3a. A layer 9 is formed on the top surface 3a. A layer 5 is formed on the top surface 3a. A layer 22 is formed on the top surface 3a. A layer 24a is formed on the top surface 3a. A layer 3c is formed on the bottom surface 3b. A layer 3 is formed on the bottom surface 3b.

[illegible]